

AMENDMENTS TO THE SPECIFICATION

On page 7, please replace the third paragraph which starts at line 5, with the following amended one:

(Aspect 4) The mask blank according to aspect 2 or 3, wherein the flatness is not greater than 0.5 μm on a flatness measurement area of the main surface on which the thin film is formed, with an area of 3mm which is laid inwardly from the boundary between the main surface and the chamfered surface exempted from the flatness measurement area, while the boundary between the main surface and the chamfered surface has the maximum height between -1 and 0 μm from the reference surface.

On page 10, please replace the first full paragraph, which starts at line 11, with the following amended one:

According to the present invention, the maximum height is between -1 μm and 0 μm . When the maximum height exceeds 0 μm , the periphery curves upward. Consequently, deformation of the reticle increases when the reticle is mounted on the substrate-holding means of the stepper. This causes a decrease in precision of the position of a transferred pattern. On the other hand, when the maximum height is less than ~~-1 μm~~ -1 μm , the substrate-holding member of the stepper cannot tightly hold the reticle. Consequently, the holding is unstable. This causes a decrease in precision of the position of a transferred pattern, which is undesirable. As miniaturization of a pattern progresses, the precision of the position of the pattern has been required to be high. Therefore, the maximum height is preferably between -0.5 μm and 0 μm ,

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more preferably between $-0.25\text{ }\mu\text{m}$ and $0\text{ }\mu\text{m}$, more preferably between $-0.1\text{ }\mu\text{m}$ and $0\text{ }\mu\text{m}$, and most preferably between $-0.05\text{ }\mu\text{m}$ and $0\text{ }\mu\text{m}$.

Please replace the paragraph bridging pages 11 and 12, with the following amended one:

According to the above-mentioned aspect 4, specifically, a flatness-measuring area defined as an area of the main surface having a thin film of the mask blank excluding a peripheral area of a width of 3 mm inward from the boundary between the main surface and the chamfered surfaces has a flatness of $0.5\text{ }\mu\text{m}$ or less, and the maximum height from a reference plane at the boundary between the main surface and the chamfered surface is between $-1\text{ }\mu\text{m}$ and $0\text{ }\mu\text{m}$. This can certainly minimize a decrease in precision of a position of a transferred pattern.